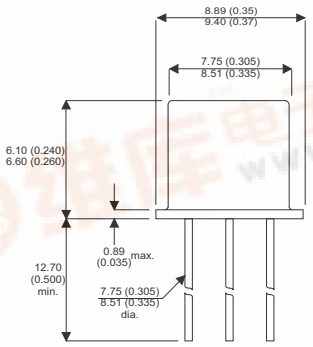
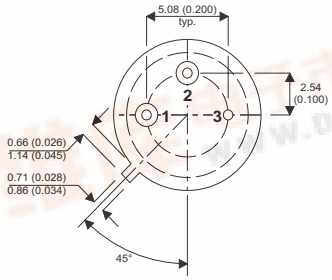
查询BFX29供应商 捷多邦，专业PCB打样工厂，24小时加急出货

SEME LAB

# BFX29

## MECHANICAL DATA
Dimensions in mm (inches)




**TO39 PACKAGE**

Pin 1 = Emitter  Pin 2 = Base  Pin 3 = Collector

# PNP SILICON EPITAXIAL TRANSISTOR

## APPLICATIONS
- General Purpose Industrial Applications

## ABSOLUTE MAXIMUM RATINGS ($T_{case}$ = 25°C unless otherwise stated)

| | | |
|---|---|---|
| $V_{CBO}$ | Collector – Base Voltage | 60V |
| $V_{CEO}$ | Collector – Emitter Voltage | 60V |
| $V_{EBO}$ | Emitter – Base Voltage | 5V |
| $I_C$ | Collector Current Continuous | 600mA |
| $I_{CM}$ | Collector Current Peak | 600mA |
| $I_{EM}$ | Emitter Current Peak | 600mA |
| $P_{tot}$ | Total Power Dissipation $T_{amb}$ < 25°C | 600 mW |
| $T_{stg}$ | Storage Temperature | –65 to 200°C |
| $T_j$ | Operating Junction Temperature | 200°C |

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# BFX29

## ELECTRICAL CHARACTERISTICS ($T_j$ = 25°C unless otherwise stated)

| | Parameter | Test Conditions | | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|---|
| $I_{EBO}$ | Emitter Cut–off Current | $V_{EB}$ = 5.0V | $I_C$ = 0 | | 30 | 500 | nA |
| | | $V_{EB}$ = 3V | $I_C$ = 0 | | 1.0 | 100 | |
| $I_{CBO}$ | Collector Cut–off Current | $V_{CB}$ =60V | $I_E$ = 0 | | 1.0 | 500 | nA |
| | | $V_{CB}$ =50V | $I_E$ = 0 | | 0.5 | 50 | |
| | | | $T_j$ = 100°C | | 0.03 | 2.0 | µA |
| $h_{FE}$ | DC Current Gain | $V_{CE}$ =10V | $I_C$ = 0.1mA | 20 | 90 | | — |
| | | $V_{CE}$ = 10V | $I_C$ = 1mA | | 40 | 105 | |
| | | $V_{CE}$ = 10V | $I_C$ = 10mA | 50 | 125 | | |
| | | $V_{CE}$ =10V | $I_C$ = 50mA | 50 | 125 | | |
| | | $V_{CE}$ = 10V | $I_C$ = 150mA | 40 | 90 | | |
| $V_{CE(sat)}$ | Collector – Emitter Saturation Voltage | $I_C$ = 150mA | $I_B$ = 15mA | | 0.15 | 0.40 | V |
| $V_{BE(sat)}$ | Base – Emitter Saturation Voltage | $I_C$ = 30mA | $I_B$ = 1.0mA | | 0.77 | 0.90 | V |
| | | $I_C$ = 150mA | $I_B$ = 15mA | | 1.05 | 1.30 | |
| $C_{tc}$ | Collector Capactitance | $V_{CB}$ = 10V | $I_E$ = $I_e$ =0 f=1.0MHz | | 6 | 12 | pF |
| $C_{te}$ | Emitter Capactitance | $V_{EB}$ = 2.0V | $I_C$ = $I_c$ =0 f=1.0MHz | | 18 | 30 | |
| $f_T$ | Transistion Frequency | $V_{CE}$ = 10V f=100MHz | $I_C$ = 50mA $T_{amb}$ = 25°C | 100 | 360 | | MHz |

## THERMAL CHARACTERISTICS

| | | | | | | |
|---|---|---|---|---|---|---|
| $R_{\theta th(j-amb)}$ | Thermal Resistance Junction to Ambient | | | | 292 | °C/W |